

CHE323/CHE384
 Chemical Processes for Micro- and Nanofabrication
www.lithoguru.com/scientist/CHE323

Lecture 29

Device Interconnect, part 2

Chris A. Mack
 Adjunct Associate Professor

Reading:
 Chapter 15, *Fabrication Engineering at the Micro- and Nanoscale*, 4th edition, Campbell


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Interconnect Delay

- The speed of a chip is a function of how fast transistors can be switched on and off, and how fast signals can propagate along the wires connecting them
- Dennard scaling
 - Transistor switching time decreased regularly till the early 2000s
 - Interconnect delay time *increased* during this time, since the length of interconnect wires has remained roughly constant
- Result: Interconnect delay is now equally or more important in determining chip speed as transistor delay

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Interconnect Delay



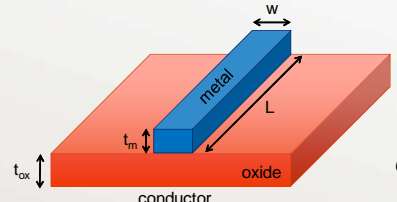
τ = rise time/fall time = interconnect delay = RC (called the "RC time constant")

$R = \text{resistance} = \text{resistivity} \frac{\text{length}}{\text{cross-section area}}$

$C = \text{capacitance} = \text{dielectric constant} \frac{\text{plate area}}{\text{gap width}}$

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Interlevel RC Time Constant



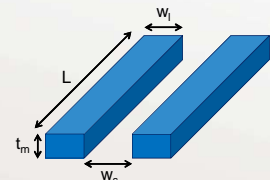
$R = \rho_m \frac{L}{wt_m}$

$C = \epsilon_{ox} \frac{wL}{t_{ox}}$

$\tau = RC = \rho_m \epsilon_{ox} \frac{L^2}{t_m t_{ox}}$

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Intralevel RC Time Constant



$R = \rho_m \frac{L}{w_l t_m}$

$C = \epsilon_{ox} \frac{t_m L}{w_s}$

$\tau = RC = \rho_m \epsilon_{ox} \frac{L^2}{w_l w_s}$

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How Can τ Be Reduced?

- Reduce metal resistivity
 - $\rho_{AL} = 2.8 \times 10^{-6} \Omega \text{ cm}$
 - $\rho_{Cu} = 1.7 \times 10^{-6} \Omega \text{ cm}$
- Reduce insulator dielectric constant
 - $\epsilon_{ox} = K_{ox} \epsilon_0$, for SiO_2 $K_{ox} = 3.9$
 - For "low-K" dielectrics, we want $K_{ox} \approx 2 - 2.5$
 - Use polymers, fluorinated oxides, porous oxides: this is very hard to do!

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WHAT STARTS HERE CHANGES THE WORLD

How Can τ Be Reduced?

3. Make t_m, t_{ox} thicker
 - Results in greater topography
 - Limited by metal line aspect ratio
4. Make metal pitch (= $w_l + w_s$) bigger
 - Requires more metal levels
5. Reduce L by using pass transistors
 - Do this when interconnect delay > 2*transistor delay

$$\tau = \rho_m \epsilon_{ox} \frac{L^2}{w_l w_s}$$

$$\tau = \rho_m \epsilon_{ox} \frac{L^2}{t_m t_{ox}}$$

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WHAT STARTS HERE CHANGES THE WORLD

Interconnect Delay

- We've switched from aluminum to copper, but from here things get exotic (carbon nanotubes, etc.)
- Low-K dielectrics are hard to make and use
 - Low-K usually results in low mechanical strength
- There is a big cost to making metal lines wider and/or thicker
- Pass transistors use up area, and so are costly

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WHAT STARTS HERE CHANGES THE WORLD

Lecture 29: What have we learned?

- Why is interconnect such a big problem today?
- What gives rise to interconnect delay?
- What are five ways to reduce interconnect delay?

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